materials

MDPI

Communication

On the Effect of the Co-Introduction of Al and Ga Impurities on the Electrical Performance of Transparent Conductive ZnO-Based Thin Films

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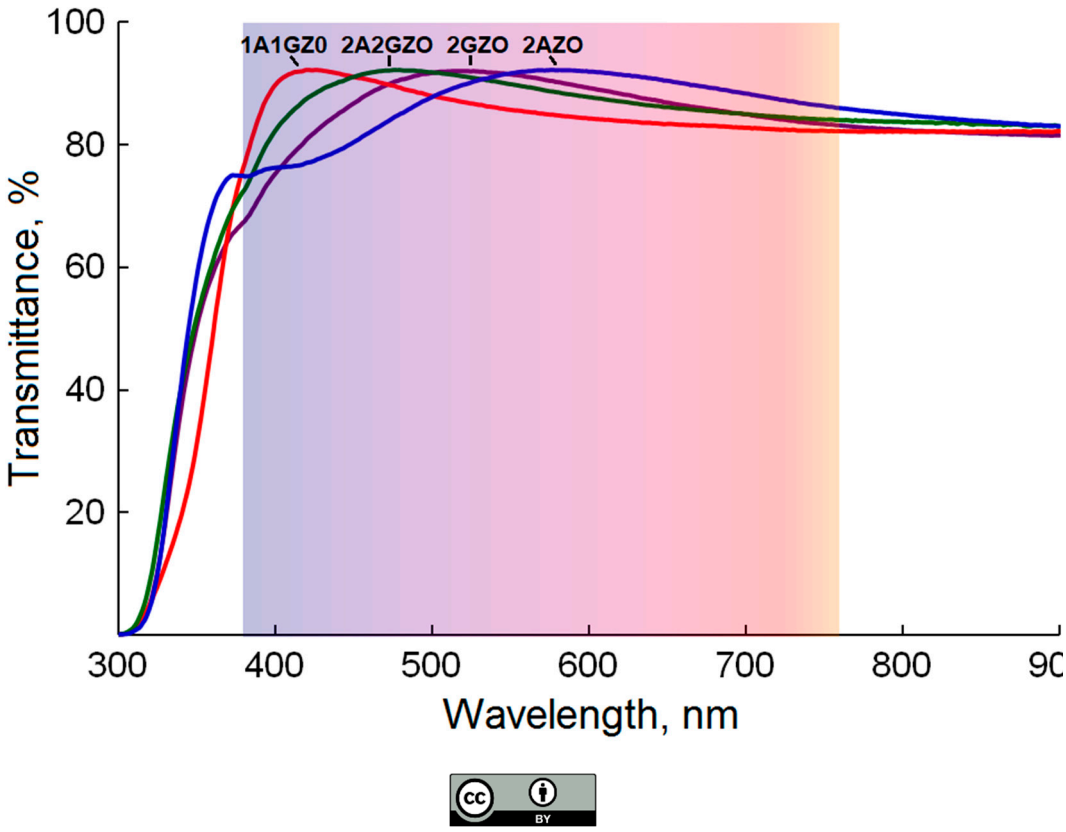

Figure S1. Transmittance spectra of glasses covered at 300°C by single-doped (2AZO, 2GZO) and co-doped (1A1GZO, 2A2GZO) thin films.

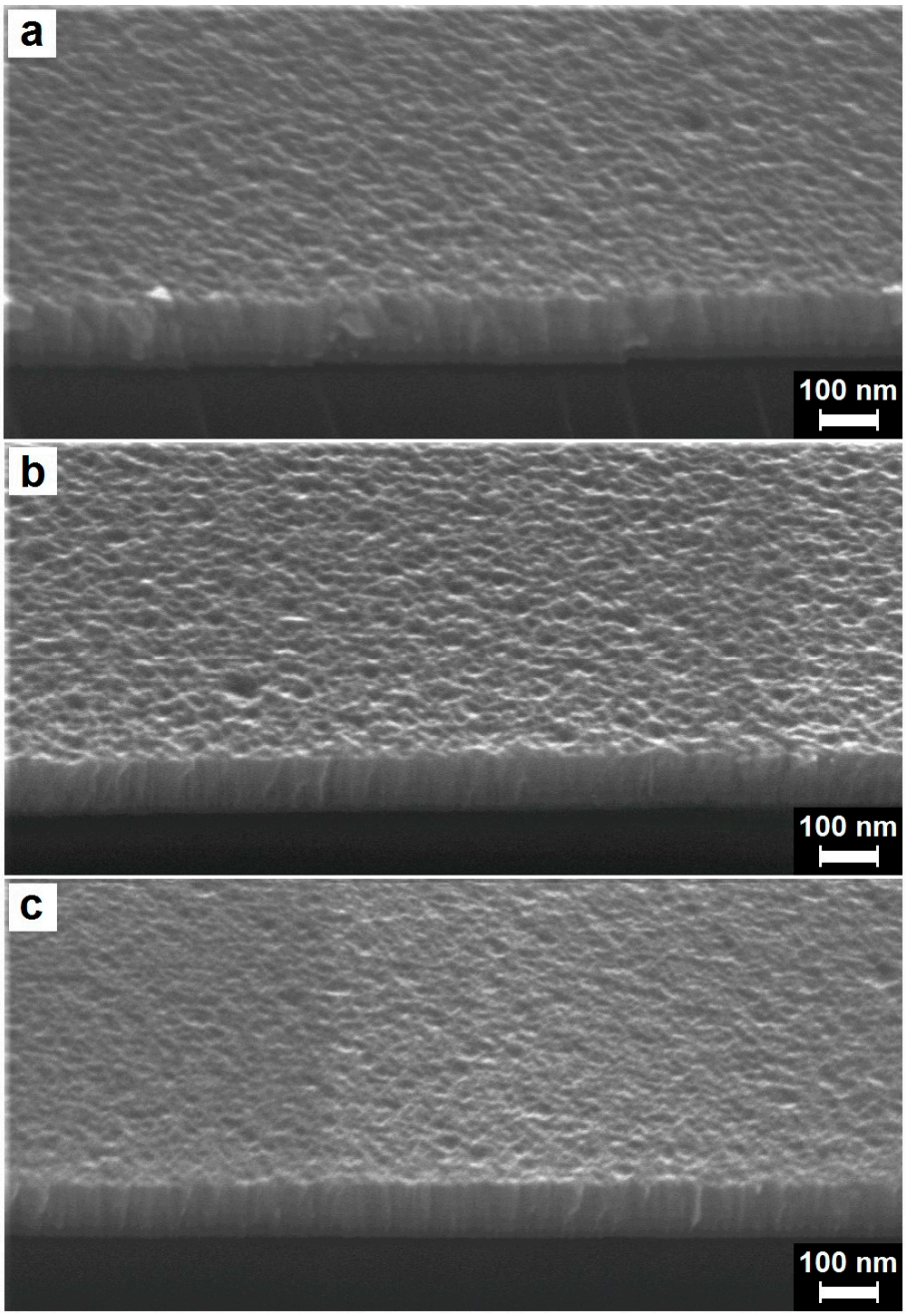

Figure S2. SEM micrographs of 2AZO (a), 2GZO (b), and 2A2GZO (c) thin films deposited at substrate temperature of 300°C.